NSN 5961-01-123-8135

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Inclosure Material:

Metal

Overall Length:

Between 0.250 inches and 0.450 inches

Overall Diameter:

0.875 inches

End Application:

An/gsq-207v1 80058

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

75.0 breakdown voltage, collector to emitter, sustained and 7.0 emitter to base voltage, static, collector open

Current Rating Per Characteristic:

Between 5.00 amperes source cutoff current and 20.00 amperes source cutoff current

Power Rating Per Characteristic:

140.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

1 case and 2 pin

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

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